# Abstracts

## Bipolar Transistor Ku-Band Oscillators with Low Phase-Noise

*C. Ansorge. "Bipolar Transistor Ku-Band Oscillators with Low Phase-Noise." 1986 MTT-S International Microwave Symposium Digest 86.1 (1986 [MWSYM]): 91-94.*

The frequency range of low cost silicon bipolar transistors can be extended using finline technique. Oscillators built up this way show high efficiency and output power up to Ku-band. The biggest advantage over the GsAs-FET is the very low phase-noise near the carrier of the bipolar oscillator.

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